



PowiGaN™ Switches Will Dominate the Market

May 2020



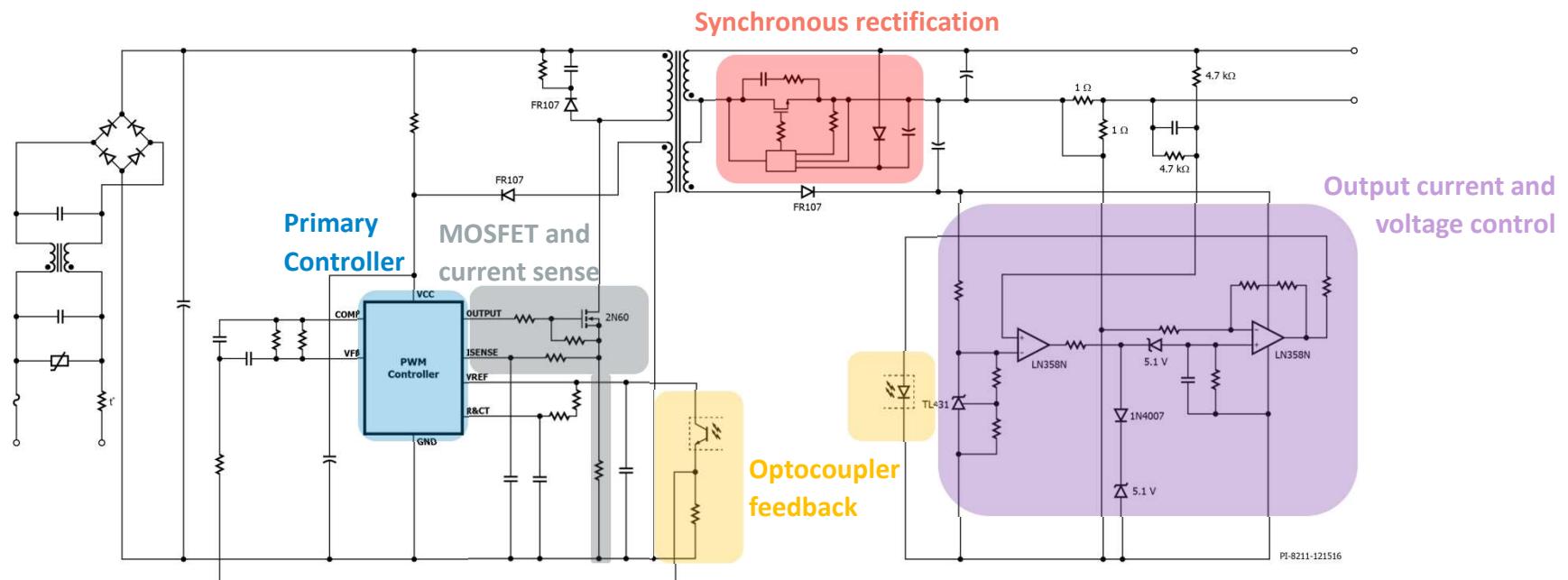
5 PI IC Families Already Feature PowiGaN Switches

- **Integrated GaN switch used across multiple families**
 - ▶ InnoSwitch™3-EP
 - ▶ InnoSwitch3-CP
 - ▶ InnoSwitch3-Pro
 - ▶ LYTSwitch™-6
 - ▶ InnoSwitch3-MX

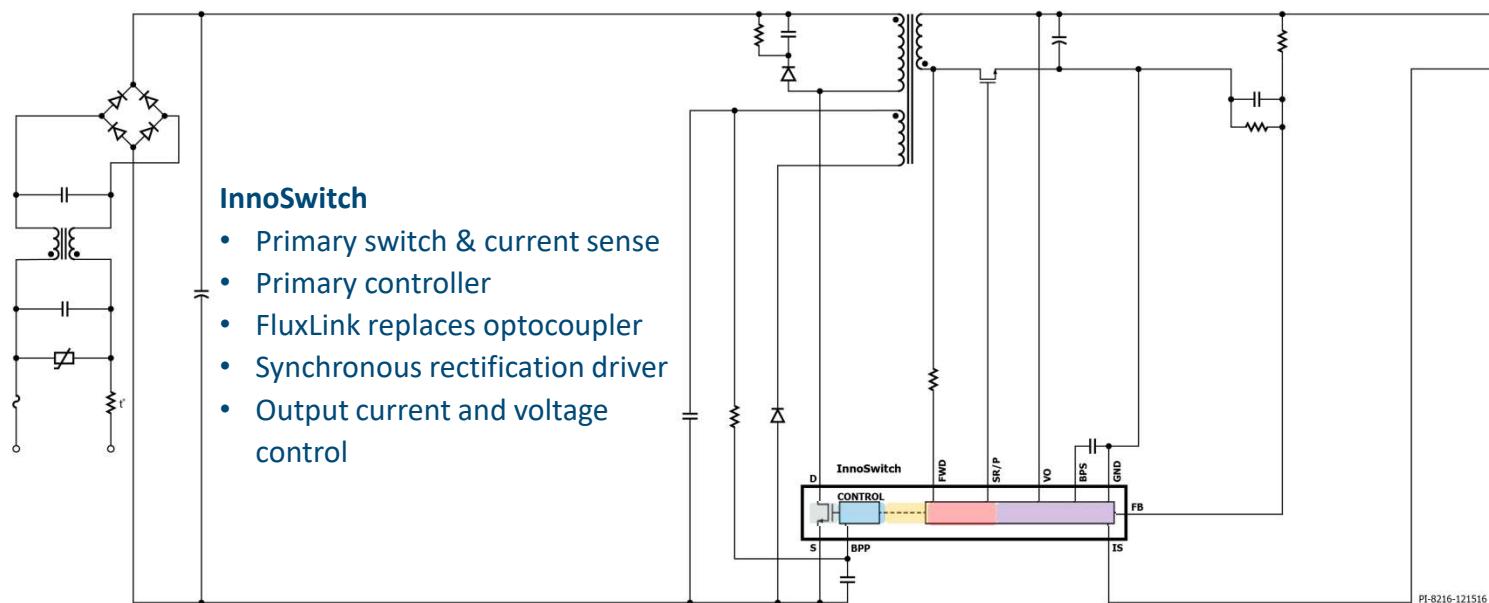


The InnoSwitch Advantage

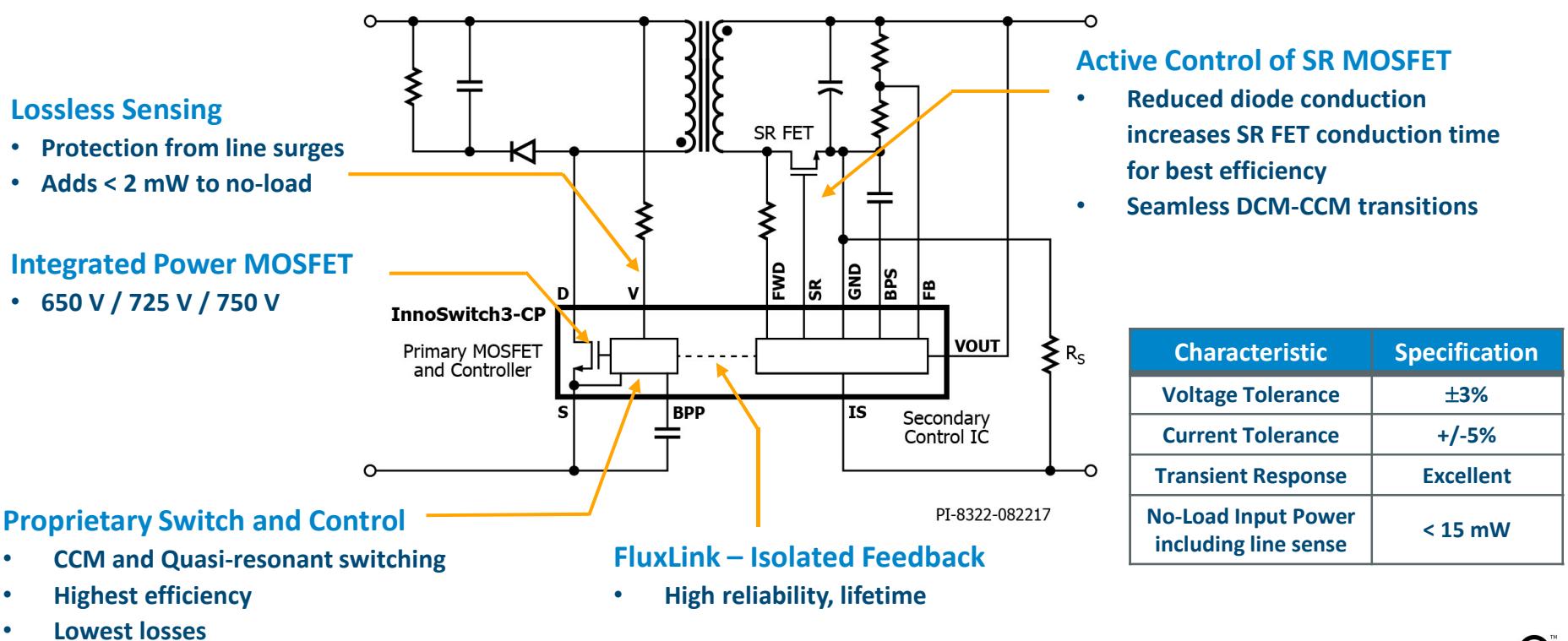
Conventional High Efficiency Charger



InnoSwitch High Efficiency Charger

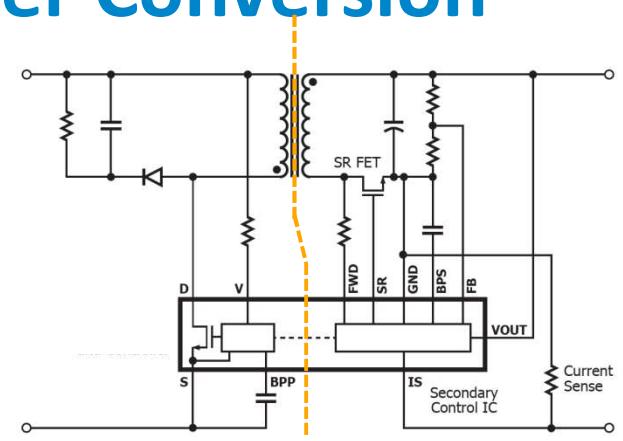


InnoSwitch-3 Isolated Flyback Employs FluxLink™ Digital Feedback to Eliminate Optocouplers

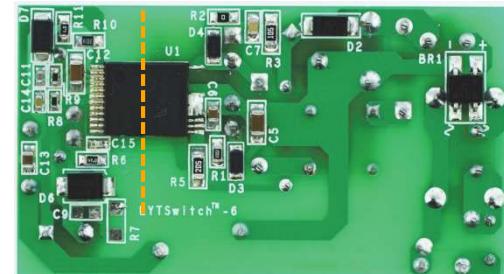


FluxLink Accurately Controls Power Conversion

- **Magneto-inductive coupling primary-to-secondary**
 - ▶ Benefits of secondary-side control
 - ▶ Simplicity of primary-side driver
 - ▶ Isolation without optocouplers
- **Crosses isolation barrier**
 - ▶ Controls both primary and secondary switching
 - Optimizes performance for highest efficiency
 - ▶ Meets all regulatory and hi-pot isolation requirements
- **Directly monitors output**
 - ▶ Accurate output voltage and current
- **Drives synchronous rectification MOSFET**
 - ▶ Simple design
 - ▶ Highly reliable under all conditions



FluxLink: Magneto-inductive coupling crosses the isolation barrier



CQC, UL and TUV certified isolation as barrier component

PowiGaN

InnoSwitch3 ICs with PowiGaN Technology

Achieve >100 W

- InnoSwitch3 silicon transistors are highly effective up to 65 W
- PowiGaN switches provide more power

- ▶ Lower $R_{DS(ON)}$ per unit area
- ▶ Lower switching losses

- PowiGaN devices

- ▶ InnoSwitch3-CP – constant power
- ▶ InnoSwitch3-EP – for open-frame
- ▶ InnoSwitch3-Pro – digital control

725 / 750 V Part Number	230 VAC +/- 15%		85 - 264 VAC	
	Adapter	Open Frame	Adapter	Open Frame
INN3x74C	20 W	25 W	15 W	20 W
INN3x75C	25 W	30 W	22 W	25 W
INN3x76C	35 W	40 W	27 W	36 W
INN3x77C	40 W	45 W	36 W	40 W
INN3x78C	70 W	75 W	55 W	65 W
INN3x79C	80 W	85 W	65 W	75 W
INN3x70C	90 W	100 W	75 W	85 W

PowiGaN switches

PowiGaN Delivers Best Performance

- **Highest efficiency conversion**

- ▶ 95% efficient – flat across line and load
- ▶ No heatsinks
- ▶ Highest power density for smart-charging adapters

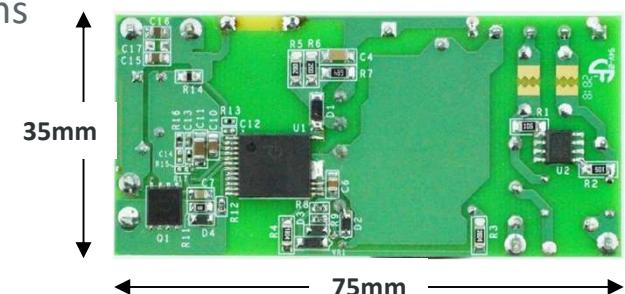


- **Safe, familiar, reliable – it just works**

- ▶ Just another switching technology from Power Integrations
- ▶ Looks and behaves like a silicon MOSFET
- ▶ No EMI challenges
- ▶ High operating voltage and increased surge margin
- ▶ Less than 40 mW no-load consumption at 265 VAC

- **In production now**

- ▶ More than 6 million parts shipped

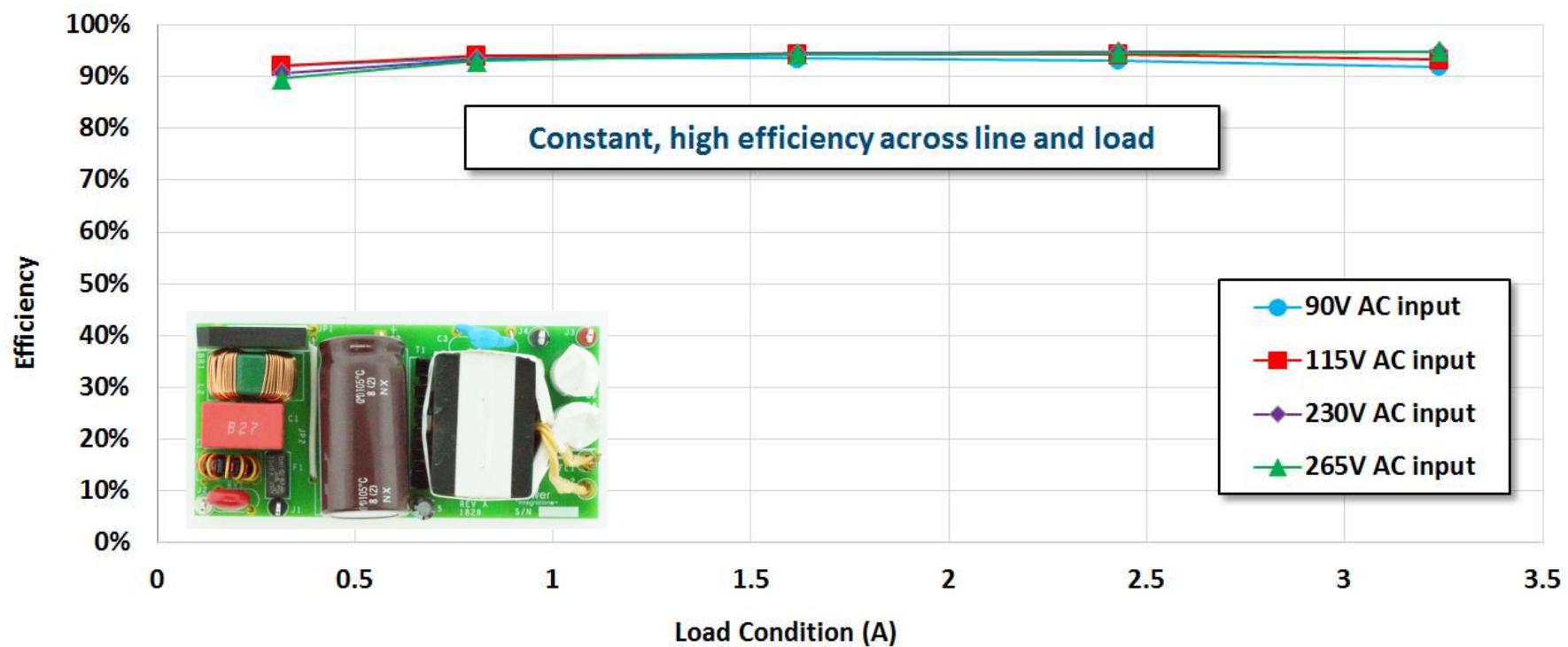


DER-747
65W 20V / 3.25A

The Small Step in Efficiency.... Got Bigger

Description	Full-Load Efficiency	Heat Energy (W)	Surface Area (Adapter)	Thermally Limited Volume
Legacy Adapter	87%	5.85	1	1
“High Efficiency” Design	90%	4.5	0.77	0.67
InnoSwitch	92%	3.6	0.62	0.48
InnoSwitch3	94%	2.7	0.48	0.3
InnoSwitch3 (with PowiGaN)	95.5%	2.0	0.35	0.21

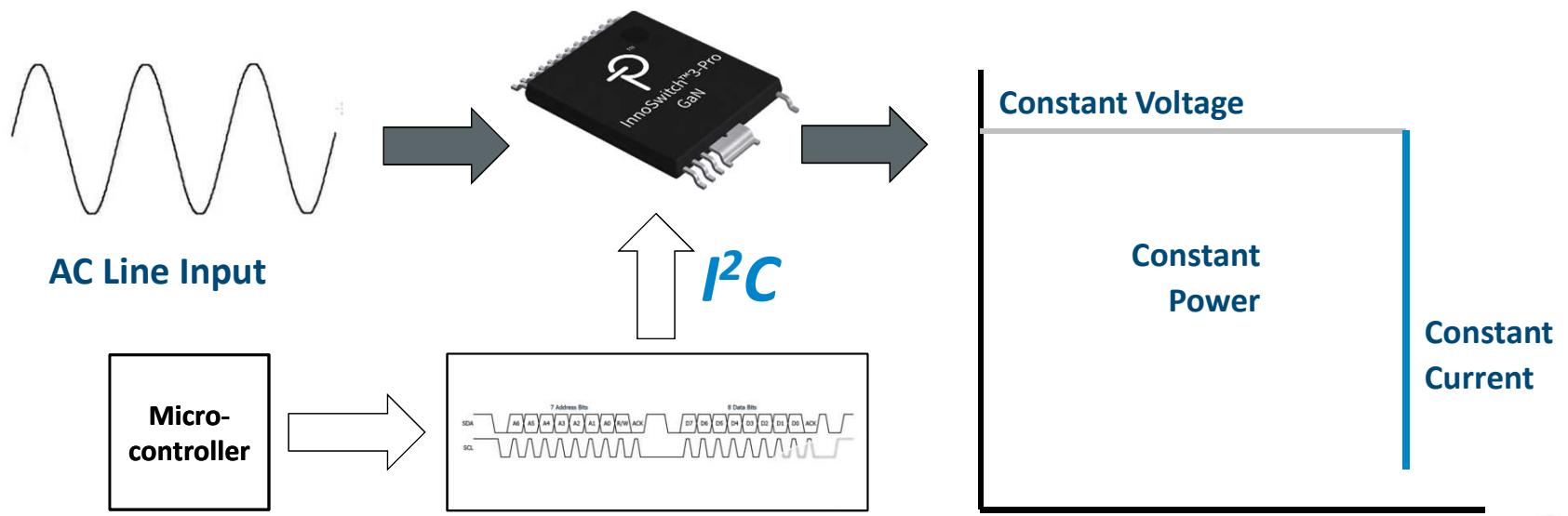
65 W DER-747 PowiGaN Constant High Efficiency Across Line and Load



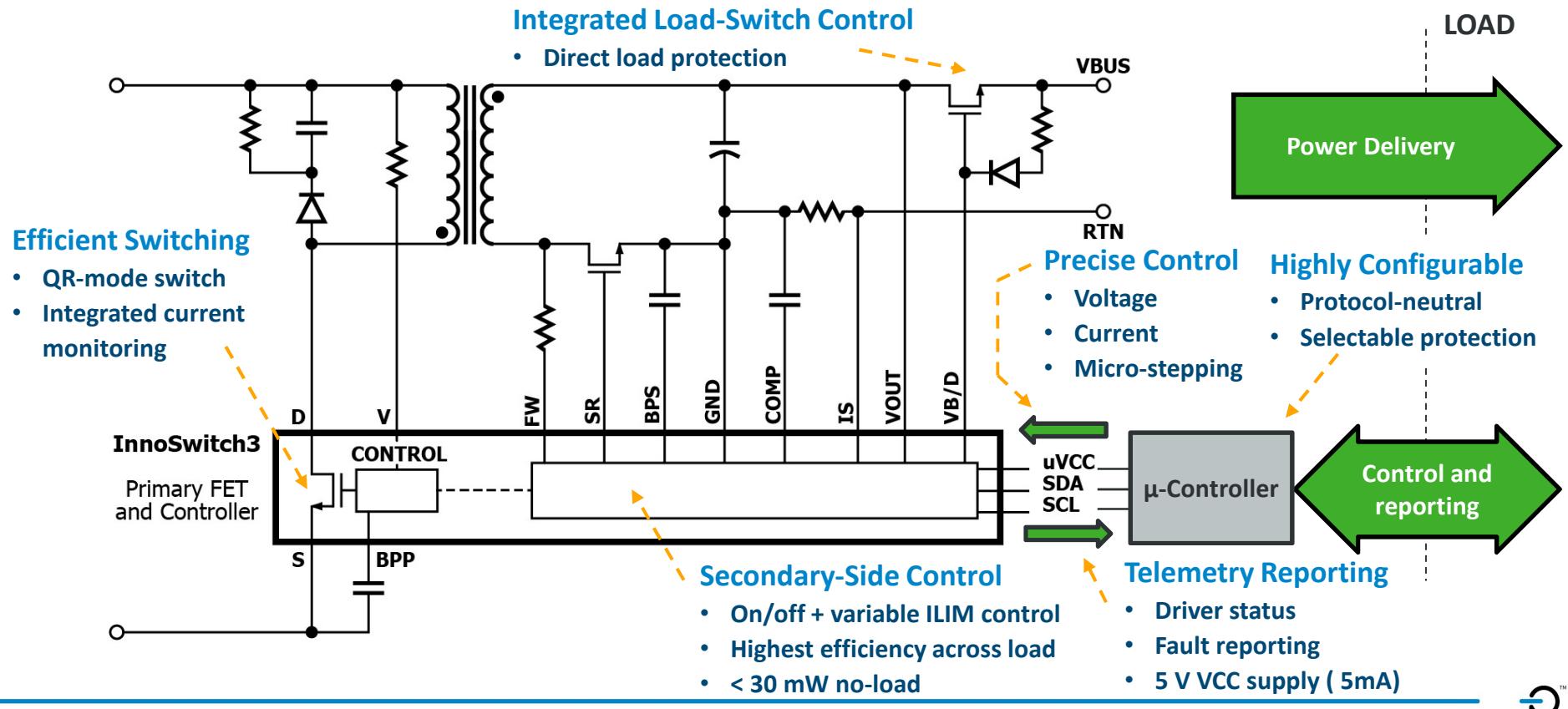
InnoSwitch3-Pro

InnoSwitch3-Pro: Digitally Programmable Power Conversion

- Advanced control engine with digital interface (I²C)
 - ▶ Output voltage and current control - CV/CC/CP output characteristic
 - ▶ Configurable protection – enable/disable, shutdown/auto-restart, trigger-points



Adding Output Control to Proven InnoSwitch3



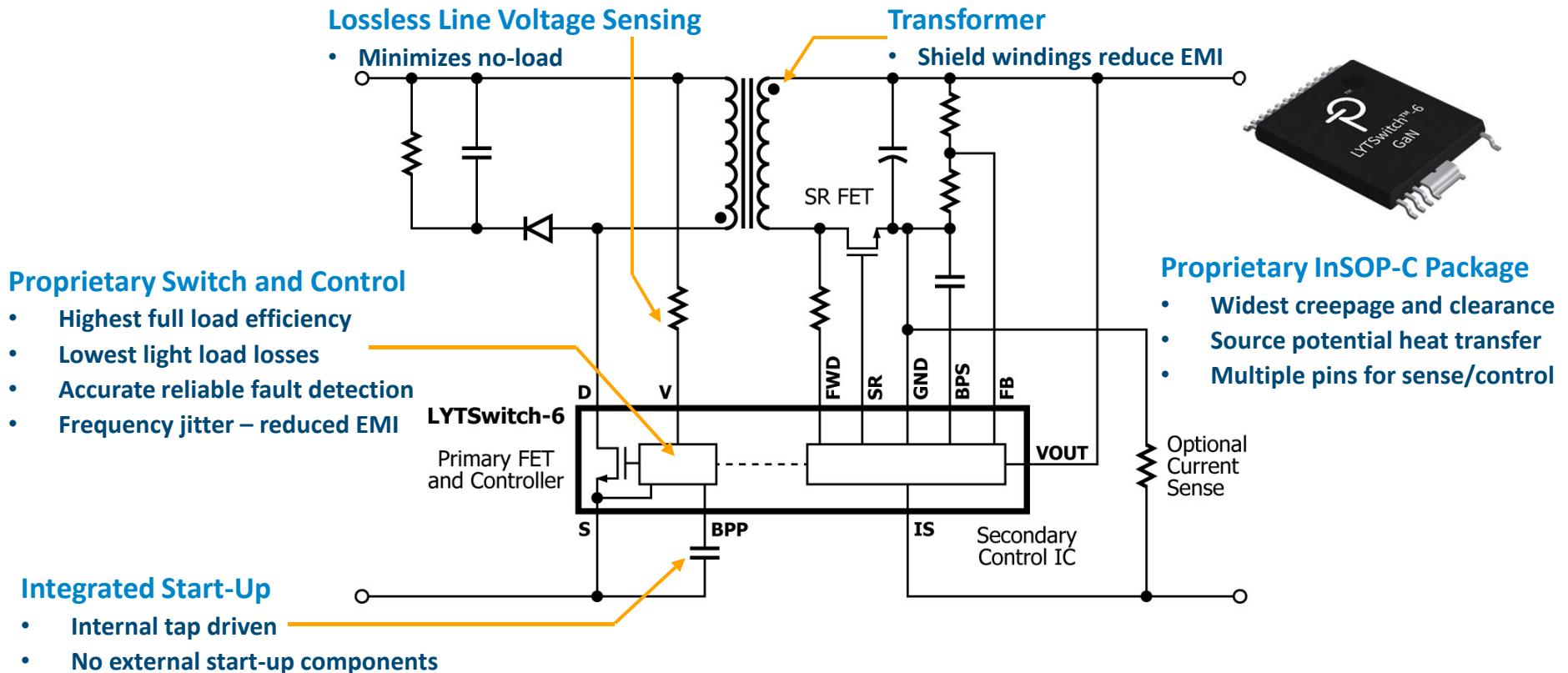
InnoSwitch3-Pro Supports a Wide Range of Applications

- **Virtually any dynamic rapid-battery-charging protocol**
 - ▶ Smart phones, notebooks/laptops/tablets, smart speakers
 - ▶ USB PD 3.0 + PPS “load-directed” charging protocol
 - ▶ Supports all rapid charge protocols including USB PD, Rapid Charge
- **Field-programmable and region-centric protection**
 - ▶ Multi-voltage lighting ballasts, DIN-rail power supplies
 - ▶ Protection features that match regional preferences
- **Programmable performance in non-charging applications**
 - ▶ Multiple solutions from single power supply design
 - ▶ Reduces design-time, reduces production, approvals and inventory costs



LYTSwitch-6

LYTSwitch-6 Uses PI Innovations for Best Performance



DER-801: 100 W Wide-Range Ballast

■ Features

- ▶ Constant voltage and constant current mode LYTSwitch-6 (LYTSwitch-6079C)
- ▶ 90-305 VAC and active PFC with HiperPFS-4
- ▶ 3-in-1 dimming (0-10 V, PWM and resistor)
 - Dimmable to 1% and dim-to-off
- ▶ Low component count
- ▶ Flicker-free operation

■ Typical Specification

- ▶ Output voltage: 48 V
- ▶ Output current: 2080 mA
- ▶ Output ripple current: <5% of nominal
- ▶ Efficiency: >90% at 230 VAC
- ▶ Power factor: >0.9 at full load
- ▶ Surge withstand: 2.5 kV differential



LYTSwitch-6: Better than the Competition

- **± 3% CV and CC output characteristic**
 - ▶ Single design covers multiple applications
- **Low no-load <15 mW (without PF)**
 - ▶ Easily meets DOE-6 and ENERGY STAR® for North America
- **Supports analog and PWM dimming**
- **Very high efficiency**
- **Fast control reduces output ripple**
 - ▶ Less output capacitance required
- **Excellent load regulation and instantaneous transient response**
 - ▶ Ideal for multi-string applications, such as RGB with highly variable independent loads

Expanding the LYTSwitch-6 Power Range

Part Number	MOSFET $V_{DS(max)}$	Output Power - Open Frame		
		277 VAC ($\pm 15\%$)	90-305 VAC	380 - 450 VDC
LYT6063C	650 V	15 W	12 W	
LYT6073C	725 V			25 W
LYT6065C	650 V	30 W	25 W	
LYT6075C	725 V			40 W
LYT6067C	650 V	50 W	45 W	
LYT6077C	725 V			60 W
LYT6068C	650 V	65 W	55 W	
LYT6078C	750 V	75 W	65 W	90 W
LYT6079C	750 V	85 W	75 W	100 W
LYT6070C	750 V	95 W	85 W	110 W



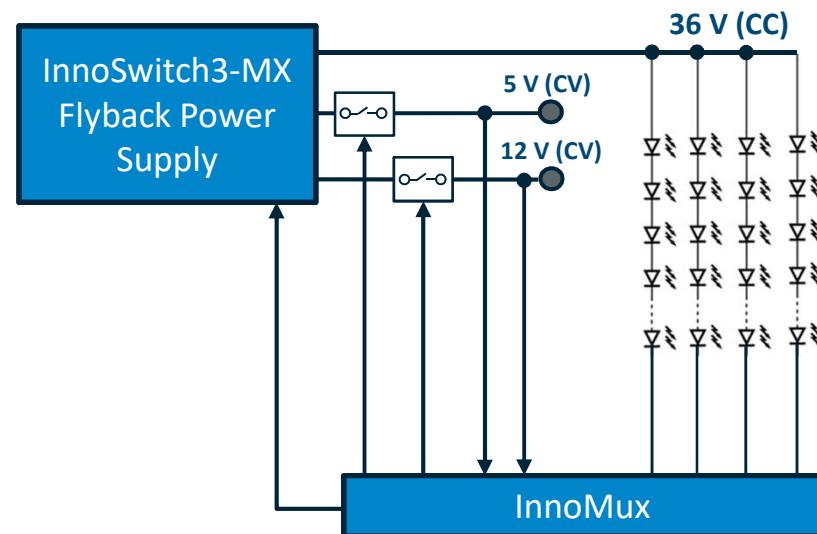
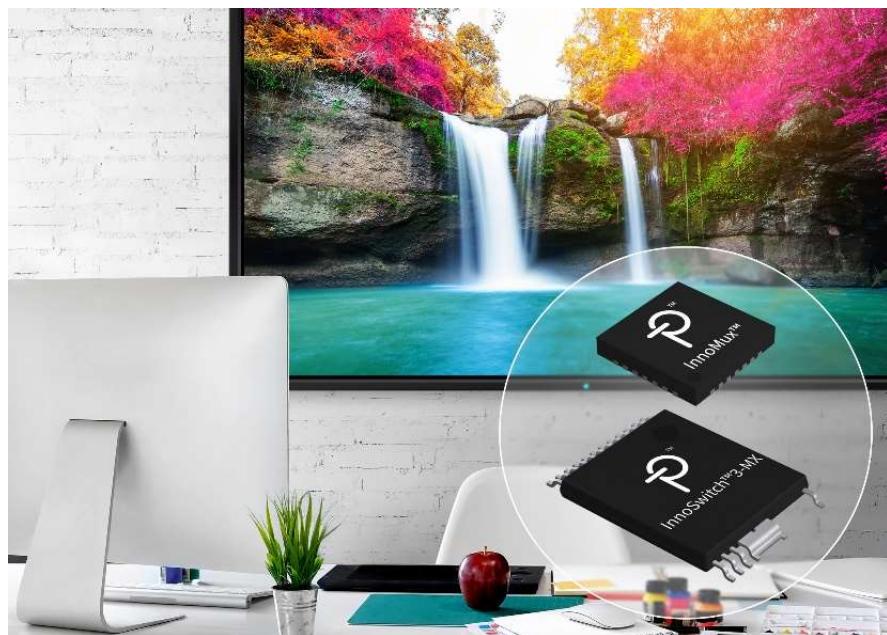
Advanced InSOP-24 package

- Reduced board space
- No heatsinks required
- Extended creepage and clearance

PowiGaN

InnoSwitch3-MX

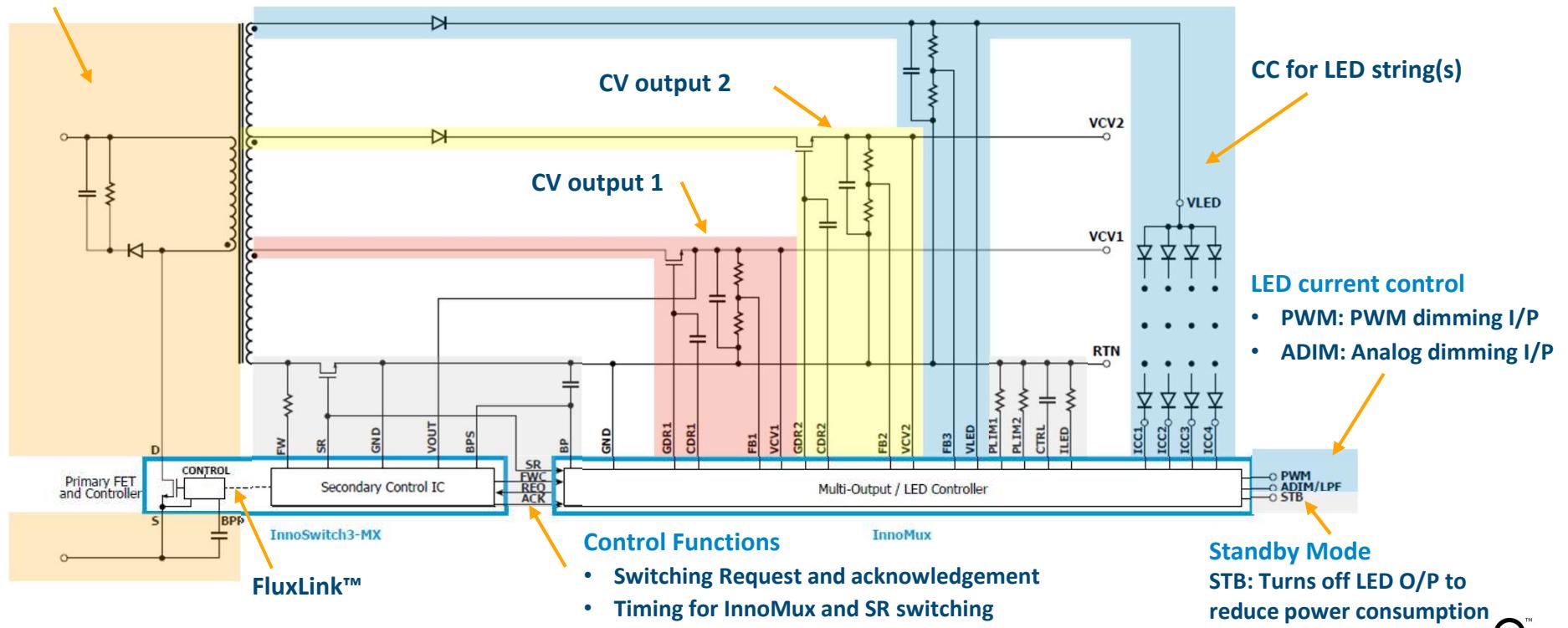
InnoMux™ A Single Stage Power Structure for Display Application



InnoSwitch3-MX Plus InnoMux Single-Stage Conversion Provides CV and CC Outputs

InnoSwitch3-MX Provides Power when Asked InnoMux IC Sends it ONLY Where Needed

Primary-side switching



InnoMux Chipset Provides Up to 75 W Output

InnoSwitch3-MX

Part Number	Primary MOSFET ($V_{DS(MAX)}$)	Power (W) 85 – 264 VAC
INN34X5C	650/725	20
INN34X6C	650/725	25
INN34X7C	650/725	32
INN3468C	650	40
INN3478C	750	55
INN3479C	750	65
INN3479C	750	75



InSOP-24D (C-Package)
MSL-3 Rated - wave solder and reflow

InnoMux

Part Number	Channels		Package
	LED strings	CV O/Ps	
IMX101J	1	1	QFN
IMX101U	1	2	HSOP
IMX102U	4	1	HSOP



QFN-28 (J-Package)
MSL-1 Rated - reflow



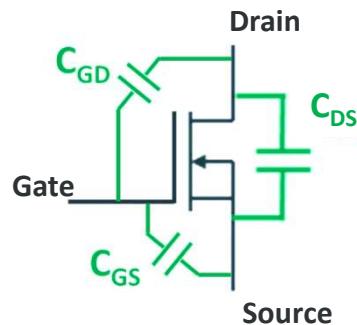
HSOP-28 (U-Package)
MSL-1 Rated – Wave Solder

Reference Design	Typical Application	Input (VAC)	Power (W)	Part Number		O/P 1 Const. Voltage	O/P 2 Const. Voltage	O/P 3 Const. Current	Dimming
				InnoSwitch3-MX	InnoMux				
DER-636	Monitors	90 - 264	40	INN3468C	IMX102U	5 V@ 3 A	-	36 V @ 0.6 A	PWM/Analog

Why GaN is Taking Over

GaN Switches Significantly Reduce Losses

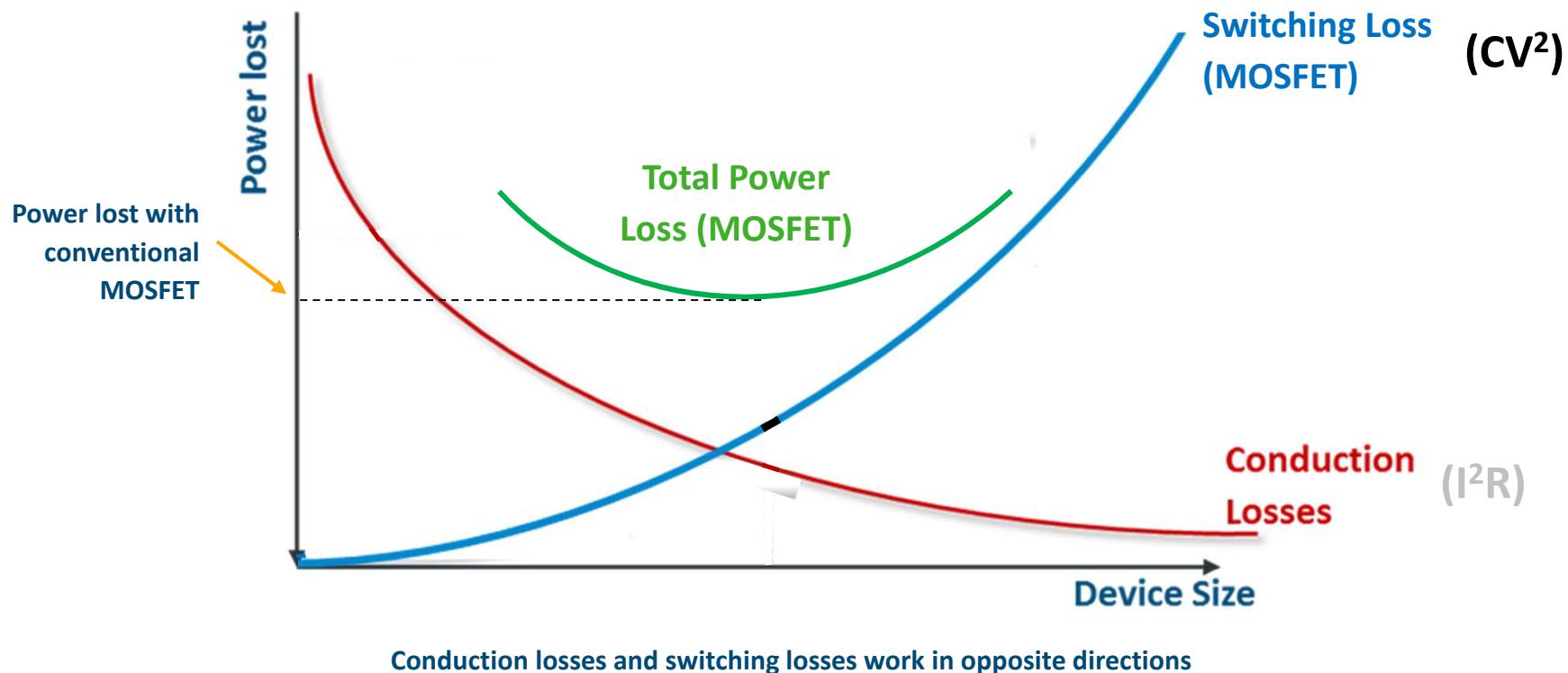
- **MOSFET output capacitance is discharged through itself at turn-on**
 - ▶ Parasitic capacitances are proportional to the size of the MOSFET
 - ▶ Bigger MOSFET = more switching loss
 - Also lower $R_{DS(ON)}$ means less conduction loss



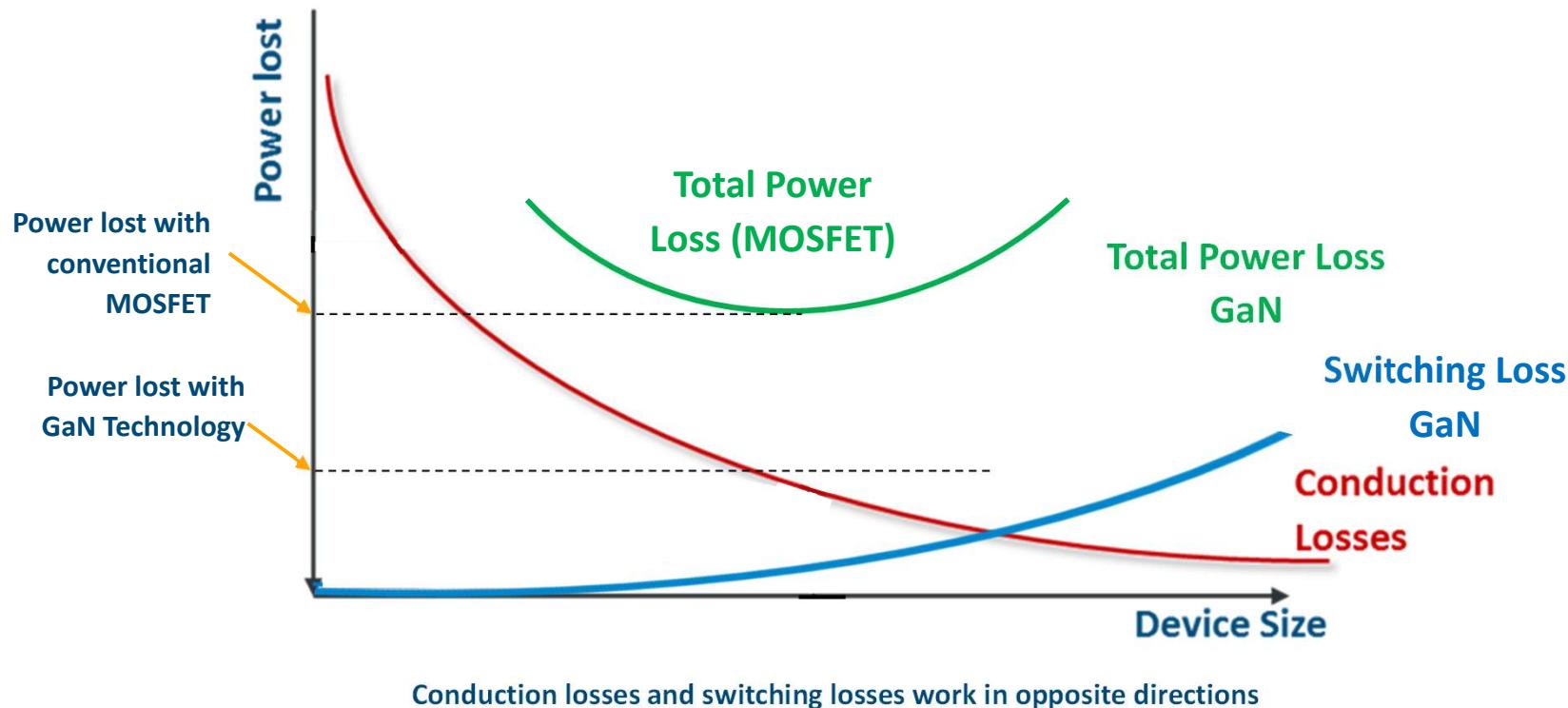
$$C_{OSS} = C_{DS} + C_{GD}$$
$$P_{(Loss)} = \frac{f \cdot C_{OSS} \cdot V^2}{2}$$

f = Switching frequency
 V = Peak of VAC ~ 400 V

Switching Losses Increase with FET Size Conduction Losses Decrease with FET Size

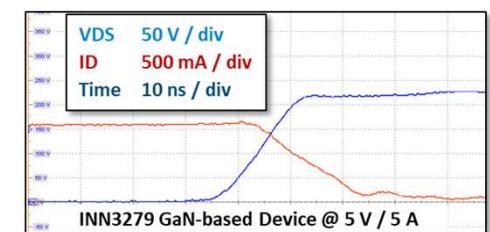
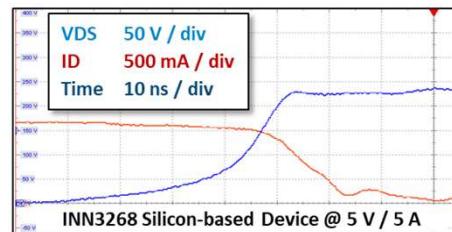


GaN Switches Change the Curve

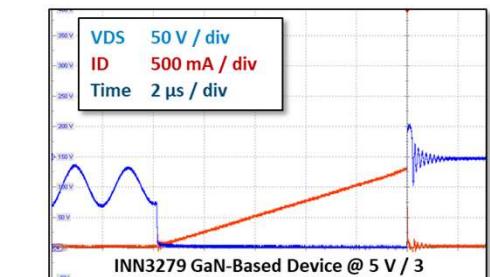
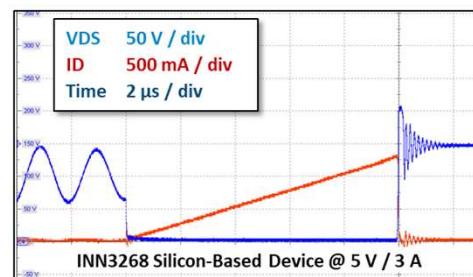


Integration Solves Fast Switching Challenges

- **Control of gate drive and circuit impedance via integration of driver stage controls switch transition rates**
 - ▶ Switch transition maximum slope same for silicon and GaN devices
 - ▶ No special EMI issues for GaN
 - ▶ Reduces fast di/dt voltage overshoot
- **Integrated switch and control stage**
 - ▶ Optimized gate drive for each switch size
 - ▶ Very accurate and fast SC/detection
 - ▶ No external current sense elements
 - Reduces circuit losses
 - ▶ Reduces circuit inductance and capacitance
 - Reduces voltage overshoot
 - No false-triggering of protection



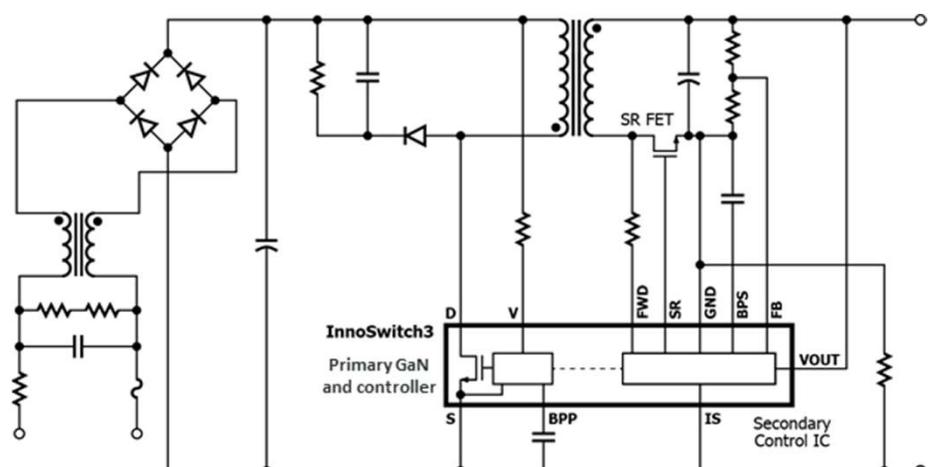
Low-line CCM Turn-off Comparison (100 V_{DC})



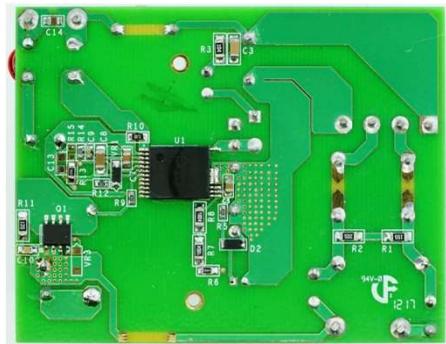
Low-line DCM Turn-on Comparison (100 V_{DC})

Integrated PowiGaN Device provides superior management of Rapid Switching

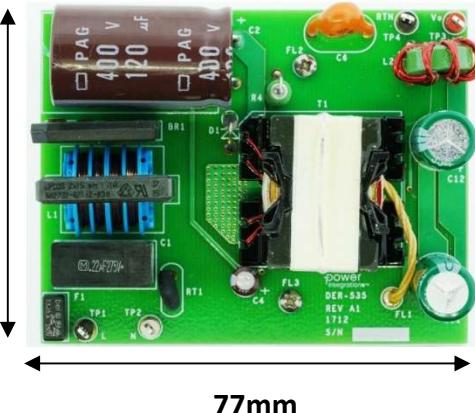
- **Driver matched to GaN switch**
 - ▶ Controls slew rate and di/dt
- **Allows integrated current limit**
 - ▶ Extremely fast control
 - ▶ No false triggering
- **Reduces parasitic components**
 - ▶ Less trace inductance
 - ▶ Reduced voltage transient spikes



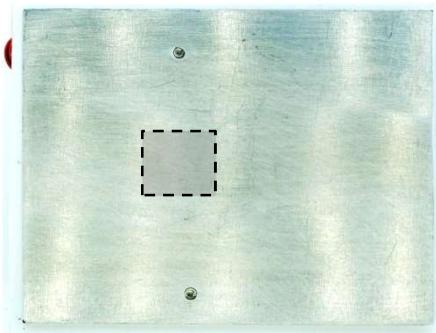
PowiGaN Technology Makes for Better Products



60 mm



DER-535
65 W 20 V / 3.25A

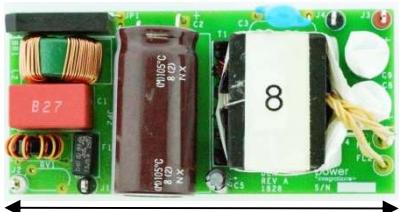


InnoSwitch3-CP
Size 8 MOSFET

InnoSwitch3-CP
Size 8 PowiGaN



35.5 mm



DER-747
65 W 20 V / 3.25A

PowiGaN is Winning in the Market

- **More GaN power devices shipped than anyone else**
 - ▶ Proprietary PI technology developed for power switching
- **Easy to use**
 - ▶ Integrated protection, drive and control eliminates challenges of discrete GaN
 - ▶ Looks like a conventional part – easy to change between designs
 - ▶ Very high reliability – More than 6 million shipped with no field failures
- **Provides major benefits across markets**
 - ▶ Smaller lighter power supplies
 - ▶ Simplifies meeting existing and emerging energy standards
 - ▶ Ideal for adapters, USB PD, industrial, and appliance



No heatsinks makes open frame /embedded power more mechanically stable



power.com



ac-dc converters



led drivers



gate drivers



motor drivers